Report No: NSWC C6054-IRLML2803-0001

Program: NASA GODDARD		Report Date: 12/31/2001		
Generic Part No.	Part Description:	Manufacturer:	•	
IRLML2803A	30V, 0.25 - $Ω$ N-Channel MOSFET	International R	Rectifier Corp.	
Package Type:	Date Code:	Package Markings		
Micro 3	0103	1B 1C		
Detailed Test Specification:	General Test Requirement:	Performance Specific	cation	
IRLML2803	None	IRLM2803 Sp	ecification Sheet	
TID Test Plan				
Serial Number:		Radiation Test Resul	lts	
1, 2, 3, 4, 5, 6, 7, 8, 9, &	10 (S/N assigned randomly)	See Appendix	B, C, D, & E	

1.0 Summary.

NAVSEA Crane was tasked to evaluate the total ionizing dose (TID) performance of a N-channel 30-V, $0.25-\Omega$ MOSFET, the IRLML2803A manufactured by International Rectifier, to conditions specified under the IRLML2803 TID Test Plan drafted by Christian Poivey, NASA-GSFC, Code 561, Greenbelt MD 20771. Specifically, NAVSEA Crane performed these tests:

a.) Electrical Measurements (I_{DSS} , $R_{DS(ON)}$, and $V_{GS(TH)}$); Total Dose Tests at 2.5, 5, 10, 20, 30, and 50 krd(Si) using a dose rate < 1 rd(Si)/s under a bias of $V_D = V_S = 0V$ and $V_G = 5V$; and Post Radiation Anneal Test for 168 hrs @ 25 °C using the same radiation fixture and biases. Electrical Measurements were performed initially and after each radiation step and following the Anneal Test.

Test results indicate that IDSS increased to a maximum of 442 nA at 50 krds and to 10.8 nA after anneal; RDSON decreased slightly to a minimum of 0.23 ohms at 50 krds but increased slightly to 0.29 ohms after anneal; and VGSTH decreased to a minimum of 0.67 V at 50 krds and to 1.15 V after anneal. Detailed radiation responses are provided in Appendix B, C, D, and E.

2.0 Applicable Documents.

g) DOD-HDBK-263

The major applicable documents	The major applicable documents, used to perform the TID tests, are listed here:			
a) IRLML2803 TID Test Plan	Specific Test Plan provided by NASA Goddard			
b) IRLML2803 Specification	Performance Specification of IRLML2803 by IR (8/25/97)			
c) <u>MIL-STD-750D</u>	Test Methods for Semiconductor Devices			
Method 1019.4	Steady State Total Dose Irradiation Procedure			
<u>Method 3400</u>	Conditions for Measurement of MOSFET Parameters			
3411.1	Gate Reverse Current (I_{G_OFF})			
3415.1	Drain Reverse Current (I _{D_OFF})			
3421.1	Static Drain to Source On Resistance (R _{DS_ON})			
3403.1	Gate to source Voltage (V_{GS_OFF})			
e) ASTM Standard E668	Standard Practice for the Application of Thermoluninscensce			
	Dosimetry (TLD) Systems for Determining Absorbed Dose in			
	Radiation Hardness Testing of Electronic Devices - Annual Book of			
	ASTM Standards, Vol. 12.02: Nuclear (II), Solar, and Geothermal			
	Energy, American Society for Testing and Materials			
f) NAVSEA INST 4734.1	NAVSEA Metrology and Calibration Program			

Handbook - Electrostatic discharge sensitive devices

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3.0 Handling Precautions.

Handling precautions were observed to minimize electrostatic discharge (ESD).

4.0 Electrical Test.

Electrical measurements were performed using a Tektronix 370 curve tracer for $V_{GS(TH)}$ and $R_{DS(ON)}$ parameters and using an automated test system consisting of two Keithley 237 SMU's and a controller for the I_{DSS} parameter. Ten samples consisting of two controls and eight test samples were characterized. These electrical test parameters were measured:

PARAMETER	CONDITION	PARAMETER	LIMIT
Zero Gate Voltage Drain	$V_{DS} = 24 \text{ V}$	$I_{ m DSS}$	< 1 µA
Current	$V_{GS} = 0 V$		·
Static Drain-Source On	$I_{DS} = 0.46 \text{ A}$	$R_{ m DS_ON}$	< 0.40 Ohm
Resistance	$V_{GS} = 4.5 \text{ V}$		
Gate Threshold Voltage	$I_{DS} = 250 \mu A$	$V_{GS(TH)}$	> 1 V
	$ m V_{DS} = m V_{GS}$		

Note: Appendix A provides a summary of a visual inspection of the test samples.

Appendix B provides a summary of the initial pre-rad electrical test measurements.

Appendix C provides a summary of the post-rad electrical test measurements.

Appendix D provides a summary of the post-anneal electrical test measurements.

Appendix E provides a graphical summary of the electrical test parameters.

4.1 Test Conditions.

Test conditions were performed as specified by the applicable documents of 2.0 (specifically, the IRLML2803 TID Test Plan). All electrical measurements were performed at an ambient room temperature of 22 $^{\circ}$ C \pm 5 $^{\circ}$ C and recorded for each test sequence.

5.0 Total Ionizing Dose (TID) Test.

Total ionizing dose tests were performed at the NAVSEA Crane Co-60 test facility using a J. L. Shepherd and Associates Model 81-22 Irradiator with a Model 484 Radiation Tunnel and Interlock Door Assembly. Test samples were placed inside a Pb/Al container to minimize dose enhancement effects caused by low-energy scattering. The desired dose rate is achieved by selecting different amounts of radioactivity and distance. For this test, the 8,000 curies source was used with the positioning table set at a distance of 670 mm.

5.1 Bias Circuit.

A custom bias board was designed and fabricated to perform the TID tests. The bias circuit conformed to the requirements of the test specification (see bias conditions - NASA IRLML2803 TID Test Plan). Figure 1 depicts the TID insitu bias circuit used for six of the eight test samples. The other two samples were biased with all leads common. Figure 2 shows the CAD layout of the TID bias board. Note that all eight test samples were exposed simultaneously.

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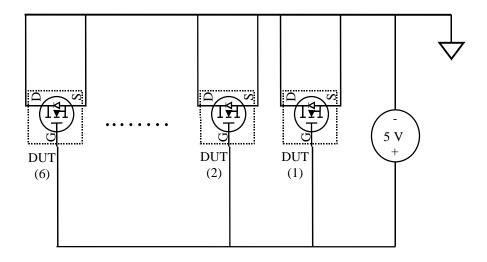


Figure 1. Insitu bias circuit used for TID test.

Top of Board (N-Channel MOSFET TID Board)

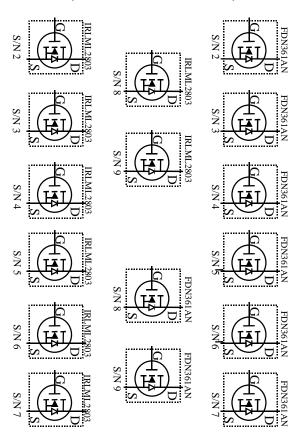


Figure 2. TID board layout of bias circuitry.

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5.2 Dosimetry.

Dosimetry standard is described in 2.0(e).

For total dose dosimetry, three ribbons were placed in a TLD holder and wrapped in a thin, (~0.001 inches) aluminum foil. The average reading of these three ribbons is used to determine the dose rate of the Co-60 source. For this test, TLDs were placed upon the top left socket, top right socket, bottom left socket, bottom right socket and the middle of all the sockets as depicted in Figure 3. Note this dosimetry was used for all subsequent tests. Table 2 provides a summary of the Co-60 Gamma Cell 220 source dosimetry.

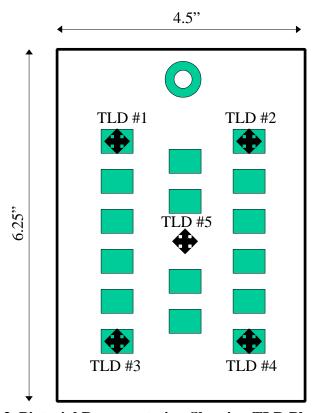


Figure 3. Pictorial Representation Showing TLD Placement.

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Inhia	Varification	of Co-60 Source
Table 4.	v Ci iiiCauwii	or co-oo bource

TLD Package	Slide Number	Avg. Dose Rd(CaF2)	Standard Deviation	Dose Rate [Rd(Si)/s]	Board Position
1	101	123.5	2.9%	0.8948	Top Left
2	102	124.2	0.6%	0.9000	Top Right
3	103	127.4	3.8%	0.9228	Bottom Left
4	104	119.7	1.4%	0.8677	Bottom Right
5	105	123.4	2.6%	0.8942	Middle
6	106	2489	1.6%	0.8861	Top Right

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Based upon the dosimetry, the dose rate was determined to be 0.89 rd(Si)/s. To validate the first radiation level (and to verify the dose rate), another TLD (top right corner) was placed upon the TID board above the top right socket. The exposure time was set for 2809 seconds ($0.89 \times 2,809 = 2,500$), resulting in an average TLD reading of 2,489 rd(Si).

Table 3 is a summary of the required exposure times to achieve radiation levels of 2.5, 5, 10, 20, 30, and 50 krd(Si) as required by the IRLML2803 TID Test Plan. Table 3 also provides the times to perform the electrical measurements between each exposure.

Table 3. Summary of Exposure and Electrical Test Times of TID Test

Total Dose Test Date	Exposure Start Time	Exposure Stop Time	Total Dose Rd(Si)	Electrical Test Start Time	Electrical Test Stop Time
12/18/2001	11:05 AM	11:51 AM	2,500	11:53 AM	12:22 PM
12/18/2001	12:25 PM	1:12 PM	5,000	1:17 PM	1:45 PM
12/18/2001	1:50 PM	3:24 PM	10,000	3:27 PM	3:58 PM
12/18/2001	4:03 PM	7:11 PM	20,000	7:13 PM	7:43 PM
12/18/2001	7:49 PM	10:56 PM	30,000	11:00 PM	11:35 PM
12/19/2001	11:52 PM	6:19 AM	50,000	6:35 AM	7:07 AM

5.3 Post-Radiation Anneal Test.

Upon completion of the last exposure (50 krd(Si)) and electrical characterization, samples were annealed for 168 hours at 25 °C under similar bias conditions. After annealing, the samples were electrically characterized again. This was specified in the IRLML2803 TID Test Plan.

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APPENDIX A. Visual Inspection Summary

Tagged S/N	Package Markings	Marking Verified	Comments
001	1B 1C	Yes	S/N Printed on DUT Card
002	1B 1C	Yes	S/N Printed on DUT Card
003	1B 1C	Yes	S/N Printed on DUT Card
004	1B 1C	Yes	S/N Printed on DUT Card
005	1B 1C	Yes	S/N Printed on DUT Card
006	1B 1C	Yes	S/N Printed on DUT Card
007	1B 1C	Yes	S/N Printed on DUT Card
008	1B 1C	Yes	S/N Printed on DUT Card
009	1B 1C	Yes	S/N Printed on DUT Card
010	1B 1C	Yes	S/N Printed on DUT Card

Note: Samples were mounted on a custom designed Device under test (DUT) card to facilitate handling and testing protocols. Serial numbers were randomly assigned and marked on each DUT card using a permanent marker.

Appendix B. Summary of Initial Electrical Test Data

	Radiation Level - 0 rd(Si)					
S/N	I_{DSS} $V_{DS} = 24V$ $V_{GS} = 0 V$ (A)	$R_{\mathrm{DS(ON)}}$ $I_{\mathrm{DS}} = 0.46~\mathrm{A}$ $V_{\mathrm{GS}} = 4.5~\mathrm{V}$ (Ohms)	$V_{GS(TH)}$ $V_{DS} = V_{GS}$ $I_{DS} = 250 \text{ mA}$ $(Volts)$	Radiation Sample Description		
001	3.75E-12	0.25	1.95	Control		
002	3.57E-12	0.28	2.18	Biased		
003	3.75E-12	0.25	1.88	Biased		
004	4.11E-12	0.26	1.95	Biased		
005	8.80E-12	0.28	2.23	Biased		
006	3.60E-12	0.28	2.17	Biased		
007	1.00E-11	0.26	1.95	Biased		
008	3.80E-12	0.25	1.98	PINS COMMON		
009	3.75E-12	0.25	1.85	PINS COMMON		
010	4.50E-12	0.28	2.2	Control		

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Appendix C. Sum	mary of Electrica	l Parameters After	each Radiation Level
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A	Appendix C. Summar	y of Electrical Paran	neters After each Radi	iation Level
		Radiation Level 2,	500 rd(Si)	
S/N	I_{DSS}	$\mathbf{R}_{\mathbf{DS}(\mathbf{ON})}$	$V_{GS(TH)}$	Radiation Sample
	(A)	(Ohms)	(Volts)	Description
001	4.20E-12	0.25	1.95	Control
002	1.90E-11	0.27	2.09	Biased
003	1.80E-11	0.25	1.8	Biased
004	2.00E-11	0.25	1.91	Biased
005	2.40E-11	0.28	2.14	Biased
006	1.90E-11	0.27	2.08	Biased
007	2.80E-11	0.25	1.87	Biased
800	1.10E-11	0.25	1.93	PINS COMMON
009	1.20E-11	0.25	1.8	PINS COMMON
010	4.70E-12	0.28	2.2	Control
		Radiation Level 5,	000 rd(Si)	
	I _{DSS}	R _{DS(ON)}	V _{GS(TH)}	Radiation
	2033	A-DS(ON)	' G5(1H)	Sample
S/N	(A)	(Ohms)	(Volts)	Description
001	4.90E-12	0.25	1.95	Control
002	6.10E-11	0.27	2.01	Biased
003	5.50E-11	0.25	1.73	Biased
004	6.20E-11	0.25	1.83	Biased
005	6.50E-11	0.27	2.06	Biased
006	5.90E-11	0.27	2	Biased
007	7.20E-11	0.25	1.8	Biased
800	2.80E-11	0.25	1.89	PINS COMMON
009	2.90E-11	0.25	1.76	PINS COMMON
010	5.30E-12	0.28	2.21	Control
		Radiation Level 10	,000 rd(Si)	
	$I_{ m DSS}$	R _{DS(ON)}	V _{GS(TH)}	Radiation
				Sample
S/N	(A)	(Ohms)	(Volts)	Description
001	4.20E-12	0.25	1.95	Control
002	1.76E-10	0.26	1.85	Biased
003	1.46E-10	0.25	1.58	Biased
004	1.68E-10	0.25	1.69	Biased
005	1.62E-10	0.27	1.91	Biased
006	1.61E-10	0.26	1.85	Biased
007	1.83E-10	0.25	1.65	Biased
800	5.60E-11	0.25	1.8	PINS COMMON
009	6.00E-11	0.25	1.67	PINS COMMON
010	5.00E-12	0.28	2.21	Control

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Appendix C. Summary of Electrical Parameters After each Radiation Level (CONT.)

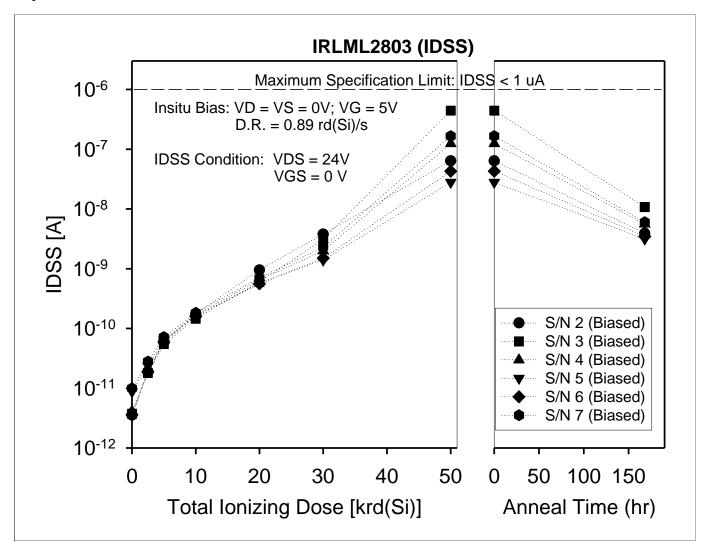
C/NI			₹7	D 11 41
S/N	I_{DSS}	$\mathbf{R}_{\mathbf{DS}(\mathbf{ON})}$	$V_{GS(TH)}$	Radiation
	(A)	(Ohms)	(Volts)	Sample Description
001	5.20E-12	0.25	1.95	Control
001	9.58E-10	0.26	1.57	Biased
002	6.03E-10	0.24	1.31	Biased
004	6.47E-10	0.24	1.42	Biased
005	5.77E-10	0.26	1.63	Biased
006	5.61E-10	0.26	1.57	Biased
007	7.04E-10	0.24	1.39	Biased
008	1.26E-10	0.25	1.64	PINS COMMOI
009	1.38E-10	0.24	1.51	PINS COMMOI
010	5.20E-12	0.28	2.21	Control
010	0.202 12	0.20	2.21	Control
		Radiation Level 30,0	000 rd(Si)	
	$I_{ m DSS}$	$\mathbf{R}_{\mathbf{DS}(\mathbf{ON})}$	$V_{GS(TH)}$	Radiation
				Sample
S/N	(A)	(Ohms)	(Volts)	Description
001	4.90E-12	0.25	1.95	Control
002	3.80E-09	0.25	1.33	Biased
003	3.10E-09	0.24	1.08	Biased
004	2.00E-09	0.24	1.18	Biased
005	1.40E-09	0.25	1.39	Biased
006	1.50E-09	0.25	1.33	Biased
007	2.30E-09	0.24	1.16	Biased
800	2.36E-10	0.24	1.5	PINS COMMOI
009	2.65E-10	0.24	1.38	PINS COMMOI
010	5.30E-12	0.28	2.21	Control
	1	Radiation Level 50,0	000 rd(Si)	1
	$\mathbf{I}_{ ext{DSS}}$	$\mathbf{R}_{\mathbf{DS}(\mathbf{ON})}$	$V_{GS(TH)}$	Radiation Sample
S/N	(A)	(Ohms)	(Volts)	Description
001	4.50E-12	0.25	1.95	Control
002	6.40E-08	0.24	0.908	Biased
003	4.42E-07	0.23	0.676	Biased
004	1.24E-07	0.23	0.782	Biased
005	2.80E-08	0.25	0.974	Biased
006	4.30E-08	0.25	0.914	Biased
007	1.66E-07	0.23	0.761	Biased
007	5.40E-10	0.24	1.266	PINS COMMOI
009	7.09E-10	0.24	1.153	PINS COMMO
010	4.60E-12	0.24	2.21	Control
010	7.00L-12	0.20	2.21	Control

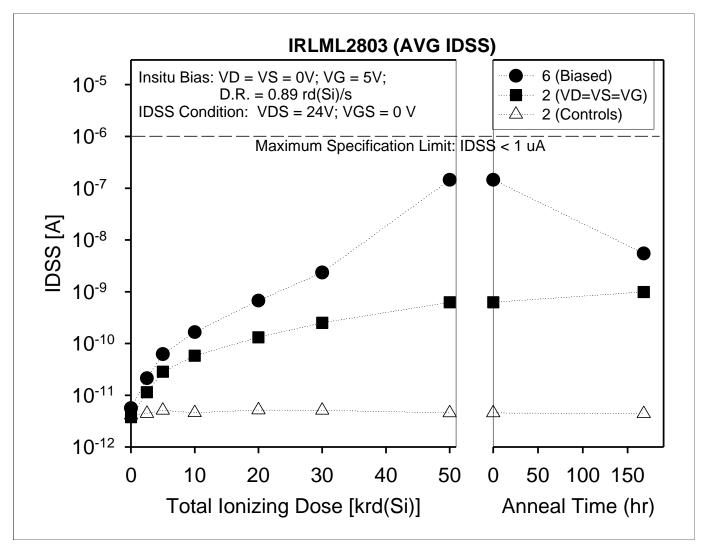
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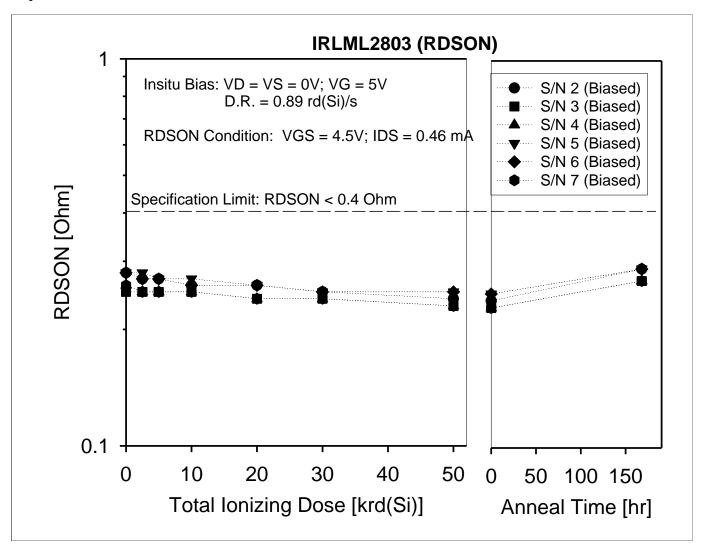
Appendix D. Summary of Electrical Tests After 168 hr Anneal

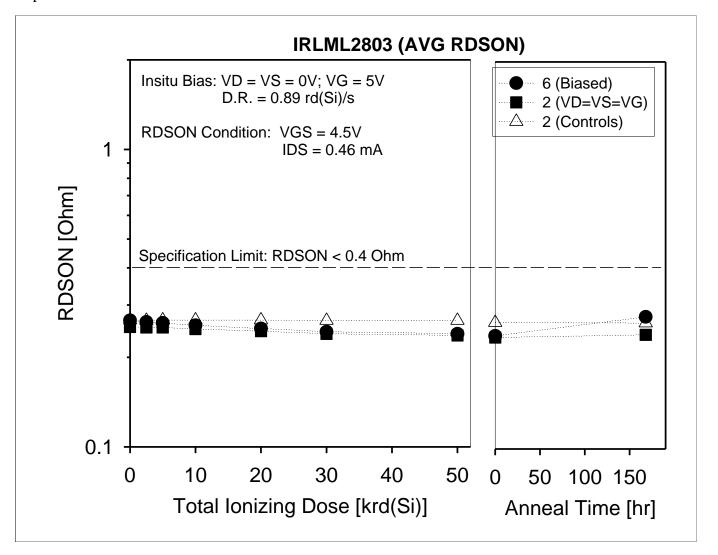
	Appendix D. Summary of Electrical Tests After 100 in Affilia				
Anneal: 168 hours @ 25 °C - (Post-rad at 50,000 rd(Si))					
S/N	I_{DSS} $V_{DS} = 24V$ $V_{GS} = 0 V$	$R_{\rm DS(ON)}$ $I_{\rm DS} = 0.46 \text{ A}$ $V_{\rm GS} = 4.5 \text{ V}$	$V_{\rm GS(TH)}$ $V_{\rm DS} = V_{\rm GS}$ $I_{\rm DS} = 250 \text{ mA}$	Radiation Sample Description	
	(A)	(Ohms)	(Volts)		
001	4.50E-12	0.25	1.96	Control	
002	3.91E-09	0.29	1.47	Biased	
003	1.08E-08	0.27	1.19	Biased	
004	5.59E-09	0.27	1.31	Biased	
005	3.15E-09	0.29	1.53	Biased	
006	3.47E-09	0.29	1.46	Biased	
007	6.01E-09	0.27	1.29	Biased	
800	7.96E-10	0.24	1.25	PINS COMMON	
009	1.18E-09	0.24	1.15	PINS COMMON	
010	4.27E-12	0.28	2.22	Control	

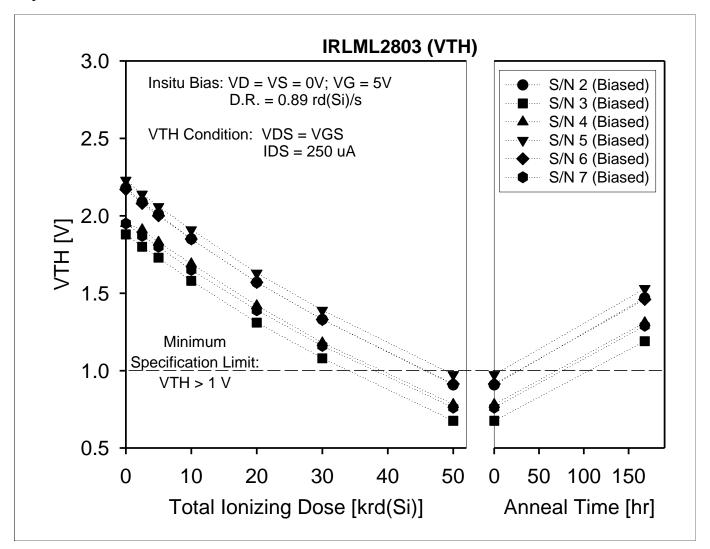
Appendix E. Graphical Summary of Electrical Tests Results

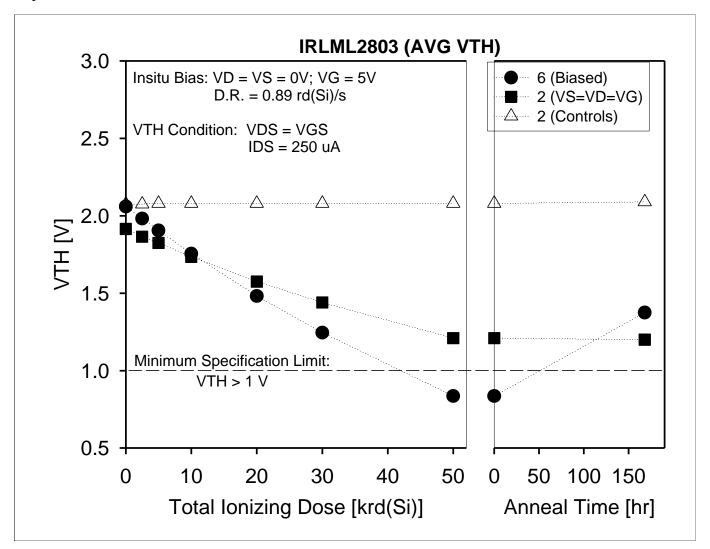












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